

isc Silicon PNP Power Transistors

BDT32F/AF/BF/CF/DF

DESCRIPTION

- DC Current Gain $-h_{FE} = 25(\text{Min})@ I_C = -1.0\text{A}$
- Collector-Emitter Sustaining Voltage-
: $V_{CEO(\text{SUS})} = -40\text{V}(\text{Min})$ - BDT32F; $-60\text{V}(\text{Min})$ - BDT32AF
 $-80\text{V}(\text{Min})$ - BDT32BF; $-100\text{V}(\text{Min})$ - BDT32CF
 $-120\text{V}(\text{Min})$ - BDT32DF
- Complement to Type BDT31F/AF/BF/CF/DF

APPLICATIONS

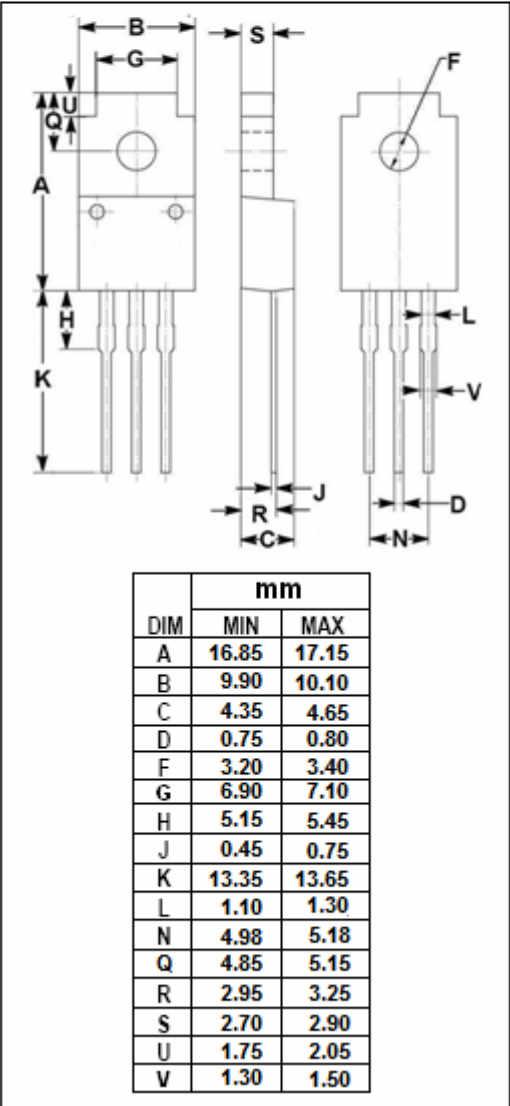
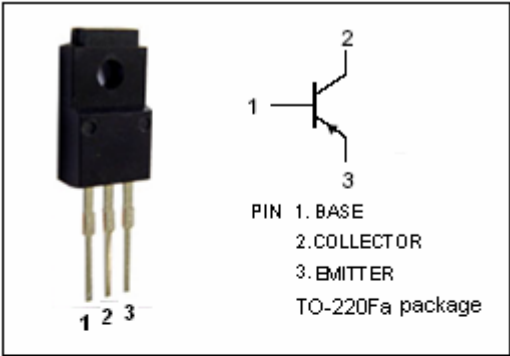
- Designed for use in audio amplifier output stages , general purpose amplifier and high speed switching applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER		VALUE	UNIT
V_{CBO}	Collector-Base Voltage	BDT32F	-80	V
		BDT32AF	-100	
		BDT32BF	-120	
		BDT32CF	-140	
		BDT32DF	-160	
V_{CEO}	Collector-Emitter Voltage	BDT32F	-40	V
		BDT32AF	-60	
		BDT32BF	-80	
		BDT32CF	-100	
		BDT32DF	-120	
V_{EBO}	Emitter-Base Voltage		-5	V
I_C	Collector Current-Continuous		-3	A
I_{CM}	Collector Current-Peak		-5	A
I_B	Base Current		-1	A
P_C	Collector Power Dissipation $T_C=25^\circ\text{C}$		22	W
T_j	Junction Temperature		150	$^\circ\text{C}$
T_{stg}	Storage Ttemperature Range		-65~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance,Junction to Case	8.12	$^\circ\text{C/W}$
$R_{th\ j-a}$	Thermal Resistance,Junction to Ambient	55	$^\circ\text{C/W}$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	BDT32F	$I_C = -30\text{mA}; I_B = 0$	-40			V
		BDT32AF		-60			
		BDT32BF		-80			
		BDT32CF		-100			
		BDT32DF		-120			
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	BDT32F/AF/BF/CF	$I_C = -3\text{A}; I_B = -0.375\text{A}$			-1.2	V
		BDT32DF	$I_C = -3\text{A}; I_B = -0.75\text{A}$			-2.5	
$V_{BE(on)}$	Base-Emitter On Voltage		$I_C = -3\text{A}; V_{CE} = -4\text{V}$			-1.8	V
I_{CES}	Collector Cutoff Current		$V_{CE} = V_{CEOmax}; V_{BE} = 0$			-0.2	mA
I_{CEO}	Collector Cutoff Current	BDT32F/AF	$V_{CE} = -30\text{V}; I_B = 0$			-0.1	mA
		BDT32BF/CF	$V_{CE} = -60\text{V}; I_B = 0$				
		BDT32DF	$V_{CE} = -90\text{V}; I_B = 0$				
I_{EBO}	Emitter Cutoff Current		$V_{EB} = -5\text{V}; I_C = 0$			-0.2	mA
h_{FE-1}	DC Current Gain		$I_C = -1\text{A}; V_{CE} = -4\text{V}$	25			
h_{FE-2}	DC Current Gain	BDT32F/AF/BF/CF	$I_C = -3\text{A}; V_{CE} = -4\text{V}$	10		50	
		BDT32DF		5			
f_T	Current-Gain—Bandwidth Product		$I_C = -0.5\text{A}; V_{CE} = -10\text{V}$	3			MHz

Switching Times

t_{on}	Turn-On Time	$I_C = -1.0\text{A}; I_{B1} = -I_{B2} = -0.1\text{A}$		0.3		μs
t_{off}	Turn-Off Time			1.0		μs